CPH3461

Power MOSFET 250V, 6.5Ω, 350mA, Single N-Channel



Features

- On-Resistance $R_{DS}(on)1=5\Omega$ (typ)
- 2.5V Drive

• ESD Diode - Protected Gate

• Low Ciss and High Speed Switching

• Pb-Free, Halogen Free and RoHS Compliance

Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	VDSS		250	V
Gate to Source Voltage	VGSS		±10	V
Drain to Gate Voltage	VDGS		250	V
Gate to Drain Voltage	VGDS		±10	V
Drain Current (DC)	ID		350	mA
Drain Current (Pulse)	I _{DP}	PW≤10µs, duty cycle≤1%	1.4	А
Power Dissipation	PD	When mounted on ceramic substrate (900mm ² \times 0.8mm)	1.0	W
Junction Temperature	Тј		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm ² ×0.8mm)	$R_{ extsf{ heta}JA}$	125	°C/W

Electrical Characteristics at $Ta = 25^{\circ}C$

Deservation	Ourseland	Question a		Value			
Parameter	Symbol Conditions		min	typ	max	Unit	
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	250			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =250V, V _{GS} =0V			1	μΑ	
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	0.4		1.3	V	
Forward Transconductance	9FS	V _{DS} =10V, I _D =170mA		1		S	
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =170mA, V _{GS} =4.5V		5	6.5	Ω	
	R _{DS} (on)2	I _D =170mA, V _{GS} =2.5V		5.1	7.2	Ω	

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ORDERING INFORMATION

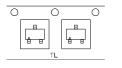
See detailed ordering and shipping information on page 2 of this data sheet.

Parameter	Symbol		Value			
		Conditions	min	typ	max	Unit
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		140		pF
Output Capacitance	Coss			8		pF
Reverse Transfer Capacitance	Crss			3		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		7.5		ns
Rise Time	tr			7.3		ns
Turn-OFF Delay Time	t _d (off)			23		ns
Fall Time	tf			43		ns
Total Gate Charge	Qg	V _{DS} =125V, V _{GS} =4.5V, I _D =350mA		2.1		nC
Gate to Source Charge	Qgs			0.3		nC
Gate to Drain "Miller" Charge	Qgd			0.7		nC
Forward Diode Voltage	VSD	IS=350mA, VGS=0V		0.79	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

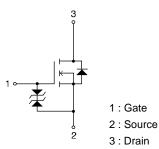
Packing Type : TL

Marking

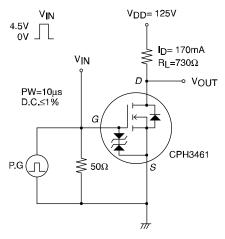




Electrical Connection

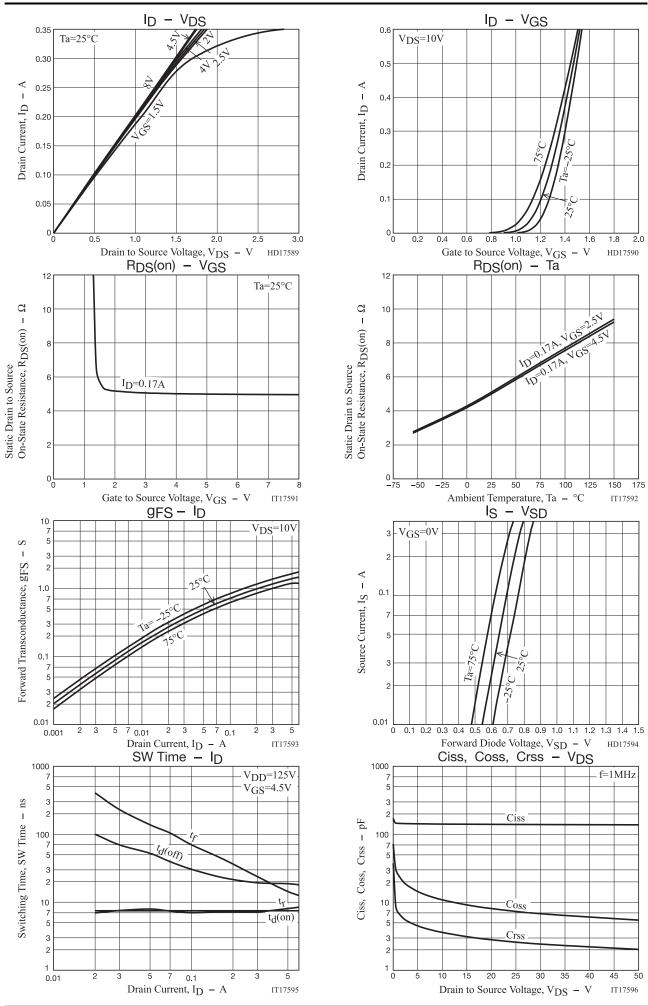


Switching Time Test Circuit

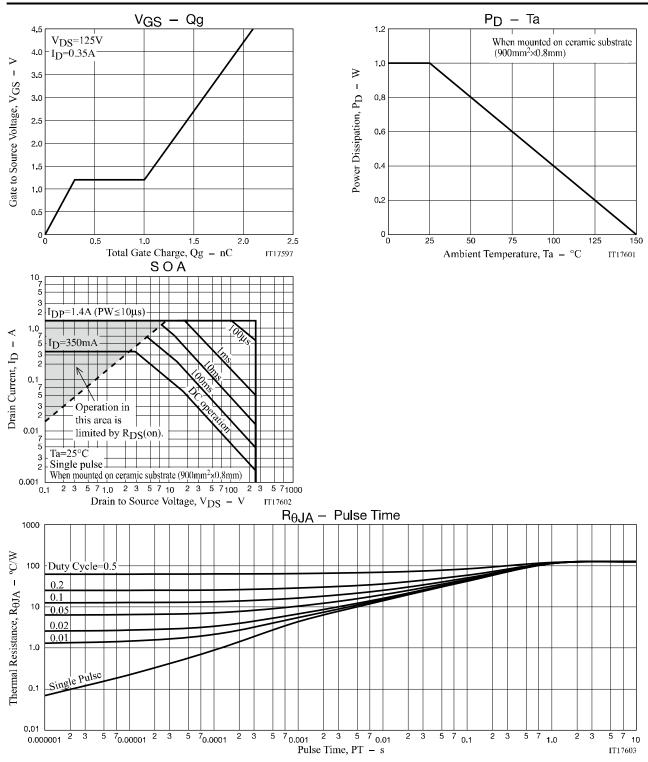


ORDERING INFORMATION

Device	Package	Shipping	Note	
CPH3461-TL-H	CPH3,SC-59	3,000pcs. / Tape & Reel		
CPH3461-TL-W	SOT-23,TO-236		Pb-Free and Halogen Free	



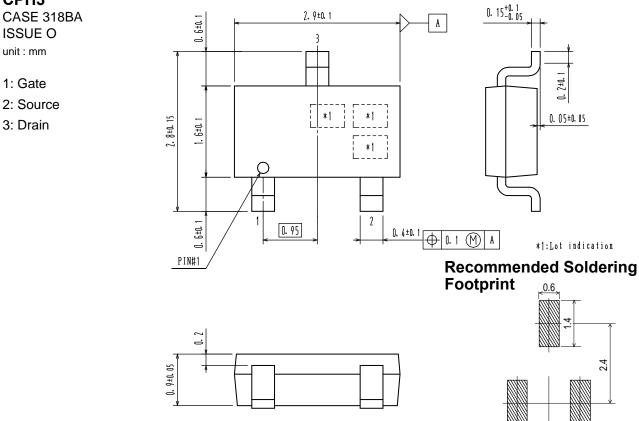
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Package Dimensions

СРН3461-ТL-Н, СРН3461-ТL-W

CPH3



0.95

0.95

Note on usage : Since the CPH3461 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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